

Honeywell Sensing and Control



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SDP8406-002

SDP Series Silicon PhotoTransistor, Side-looking Plastic Package



Representative photograph, actual product appearance may vary.

Features

Side-looking plastic package
 50 ° (nominal) acceptance angle
 Wide sensitivity ranges
 Mechanically and spectrally matched to SEP8506 and SEP8706 infrared emitting diodes

Description

The SDP8406 is an NPN silicon phototransistor molded in a side-looking clear plastic package. The chip is positioned to accept radiation through a plastic lens from the side of the package.

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Product Specifications

| | |
|---|---|
| Product Type | IR Component |
| Angular Response (Degree) | 50 |
| Light Current Minimum | 1.80 mA |
| Light Current Maximum | 3.60 mA |
| Package Style | Side-Looking |
| Package Components | Plastic |
| Package Color | Clear |
| Rise and Fall Time | 15 μs |
| Power Dissipation | 100 mW |
| Operating Temperature Range | -40 °C to 85 °C [-40 °F to 185 °F] |
| Dark Current | 100 nA |
| Collector-Emitter Breakdown Voltage | 30 V |
| Emitter-Collector Breakdown Voltage | 5 V |
| Collector-Emitter Saturation Voltage | 0.4 V |
| Comment | The radiation source is a tungsten lamp operating at a color temperature of 2870°K. |
| Availability | Global |
| Product Name | Phototransistor |

Due to regional agency approval requirements, some products may not be available in your area. Please contact your regional Honeywell office regarding your product of choice.